

KSP05/06

Amplifier Transistor

- Collector-Emitter Voltage: V_{CEO} = KSP05: 60V
- Collector Dissipation: P_C (max)=625mW
 Complement to KSP55/56



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector Base Voltage		
	: KSP05	60	V
	: KSP06	80	V
V _{CEO}	Collector-Emitter Voltage		
	: KSP05	60	V
	: KSP06	80	V
V_{EBO}	Emitter-Base Voltage	4	V
l _C	Collector Current	500	mA
P _C	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55~150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =1mA, I _B =0			
	: KSP05		60		V
	: KSP06		80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =100μA, I _C =0	4		V
I _{CBO}	Collector Cut-off Current				
	: KSP05	V_{CB} =60V, I_{E} =0		0.1	μΑ
	: KSP06	V _{CB} =80V, I _E =0		0.1	μΑ
I _{CEO}	Collector Cut-off Current	V _{CE} =60V, I _B =0		0.1	μΑ
h _{FF}	DC Current Gain	V _{CE} =1V, I _C =10mA	50		
		V _{CE} =1V, I _C =100mA	50		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =100mA, I _B =10mA		0.25	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =1V, I _C =100mA		1.2	V
f _T	Current Gain Bandwidth Product	V _{CE} =2V, I _C =10mA f=100MHz	100		MHz

^{*} Pulse Test: PW≤300μs, Duty Cycle≤2%

Typical Characteristics

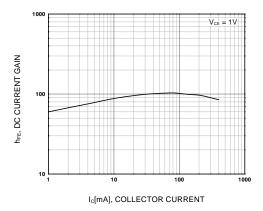


Figure 1. DC current Gain

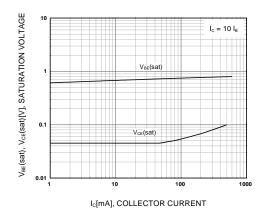


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

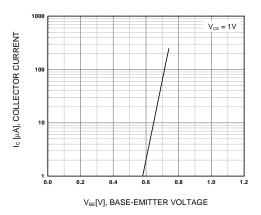


Figure 3. Base-Emitter On Voltage

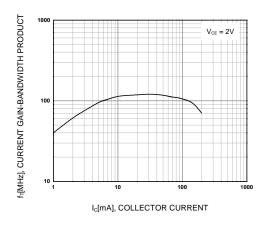
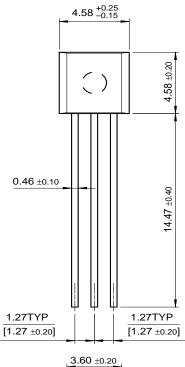


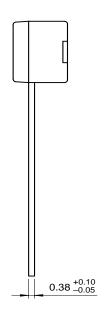
Figure 4. Current Gain Bandwidth Product

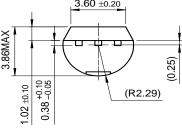


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